

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	97502	semiconductor and (recess or groove or trench)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2002/02/13 14:21
2	BRS	L2	36807	1 and well	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2002/02/13 14:27
3	BRS	L3	1684	2 and (buried adj (layer or region))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2002/02/13 14:28
4	BRS	L4	1324	3 and isolat\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2002/02/13 14:29
5	BRS	L5	441	4 and memory	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2002/02/13 14:29

	Comments	Error Definition	Errors
1			0
2			0
3			0
4			0
5			0

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	119	5 and (n adj well) and (p adj well)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2002/02/13 14:30

	Comments	Error Definition	Errors
6			0